

BSS84AKS

50 V, 160 mA dual P-channel Trench MOSFET

Rev. 1 — 23 May 2011

Product data sheet

1. Product profile

1.1 General description

Dual P-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) package using Trench MOSFET technology.

1.2 Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- ESD protection up to 1 kV
- AEC-Q101 qualified

1.3 Applications

- Relay driver
- High-speed line driver

- High-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per trans	istor						
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	-50	V
V_{GS}	gate-source voltage			-20	-	20	V
I_D	drain current	$V_{GS} = -10 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	-	-	-160	mA
Static ch	aracteristics (per transist	or)					
R _{DSon}	drain-source on-state resistance	V_{GS} = -10 V; I_{D} = -100 mA; T_{j} = 25 °C		-	4.5	7.5	Ω

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



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2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source 1	D. D. D.	D4
2	G1	gate 1	6 5 4	D1 D2
3	D2	drain 2		
4	S2	source 2	0	G1 + G2
5	G2	gate 2	□1 □2 □3	
6	D1	drain 1	SOT363 (TSSOP6)	S1 S2 sym147

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BSS84AKS	TSSOP6	plastic surface-mounted package; 6 leads	SOT363

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
BSS84AKS	%VY

[1] % = placeholder for manufacturing site code

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5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Doromotor	Conditions		Min	Mov	Unit
Parameter	Conditions		IVIII	IVIAX	Unit
drain-source voltage	$T_j = 25 ^{\circ}C$		-	-50	V
gate-source voltage			-20	20	٧
drain current	$V_{GS} = -10 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	-	-160	mA
	V _{GS} = -10 V; T _{amb} = 100 °C	[1]	-	-100	mΑ
peak drain current	$T_{amb} = 25 ^{\circ}C$; single pulse; $t_p \le 10 \mu s$		-	-640	mA
total power dissipation	T _{amb} = 25 °C	[2]	-	280	mW
			-	320	mW
	T _{sp} = 25 °C		-	990	mW
total power dissipation	T _{amb} = 25 °C	[2]	-	445	mW
junction temperature			-55	150	°C
ambient temperature			-55	150	°C
storage temperature			-65	150	°C
liode					
source current	T _{amb} = 25 °C	[1]	-	-160	mA
rating					
electrostatic discharge voltage	НВМ	[3]	-	1000	٧
	gate-source voltage drain current peak drain current total power dissipation total power dissipation junction temperature ambient temperature storage temperature liode source current rating	$ \begin{array}{lll} \text{drain-source voltage} & T_{j} = 25 \ ^{\circ}\text{C} \\ \\ \text{gate-source voltage} \\ \\ \text{drain current} & V_{GS} = -10 \ \text{V}; \ T_{amb} = 25 \ ^{\circ}\text{C} \\ \\ \hline V_{GS} = -10 \ \text{V}; \ T_{amb} = 100 \ ^{\circ}\text{C} \\ \\ \text{peak drain current} & T_{amb} = 25 \ ^{\circ}\text{C}; \ \text{single pulse}; \ t_{p} \leq 10 \ \mu\text{s} \\ \\ \hline total \ \text{power dissipation} & T_{amb} = 25 \ ^{\circ}\text{C} \\ \\ \hline \text{total power dissipation} & T_{amb} = 25 \ ^{\circ}\text{C} \\ \\ \hline \text{total power dissipation} & T_{amb} = 25 \ ^{\circ}\text{C} \\ \\ \hline \text{junction temperature} \\ \\ \hline \text{ambient temperature} \\ \\ \hline \text{storage temperature} \\ \hline \\ \hline \text{liode} \\ \\ \hline \text{source current} & T_{amb} = 25 \ ^{\circ}\text{C} \\ \hline \\ \hline \\ \hline \text{rating} \\ \hline \end{array} $	$ \begin{array}{c} \text{drain-source voltage} \\ \text{gate-source voltage} \\ \text{drain current} \\ \end{array} \begin{array}{c} V_{GS} = -10 \text{ V}; T_{amb} = 25 \text{ °C} \\ \hline V_{GS} = -10 \text{ V}; T_{amb} = 100 \text{ °C} \\ \hline V_{GS} = -10 \text{ V}; T_{amb} = 100 \text{ °C} \\ \hline \end{array} \begin{array}{c} \text{[1]} \\ \text{peak drain current} \\ \text{total power dissipation} \\ \hline T_{amb} = 25 \text{ °C}; \text{single pulse}; t_p \leq 10 \text{ µs} \\ \hline \hline T_{amb} = 25 \text{ °C} \\ \hline \end{array} $ $ \begin{array}{c} \text{[2]} \\ \hline \text{[1]} \\ \hline T_{sp} = 25 \text{ °C} \\ \hline \end{array} $ $ \begin{array}{c} \text{[2]} \\ \text{junction temperature} \\ \text{ambient temperature} \\ \text{storage temperature} \\ \hline \\ \text{iode} \\ \hline \end{array} $ source current $ \begin{array}{c} T_{amb} = 25 \text{ °C} \\ \hline \end{array} \begin{array}{c} \text{[2]} \\ \hline \end{array} $	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².

^[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[3] Measured between all pins.

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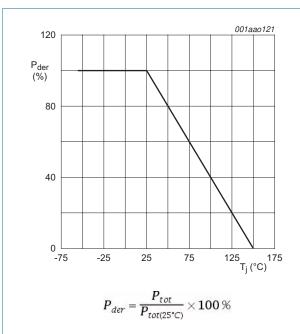


Fig 1. Normalized total power dissipation as a function of junction temperature

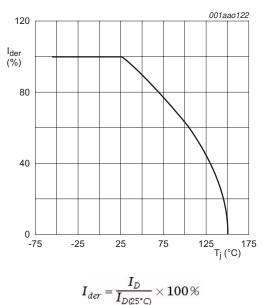
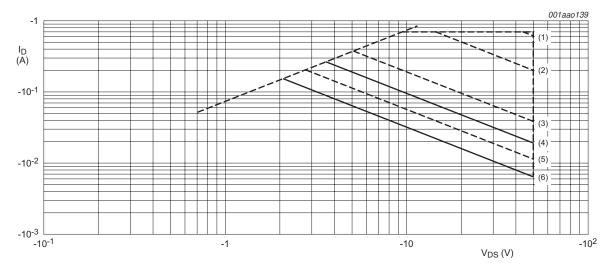


Fig 2. Normalized continuous drain current as a function of junction temperature



I_{DM} is single pulse

(1) $t_p = 100 \ \mu s$

(2) $t_p = 1 \text{ ms}$

(3) $t_p = 10 \text{ ms}$

(4) DC; $T_{sp} = 25$ °C

 $(5) t_p = 100 ms$

(6) DC; $T_{amb} = 25 \, ^{\circ}\text{C}$; drain mounting pad 1 cm²

Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source Fig 3. voltage

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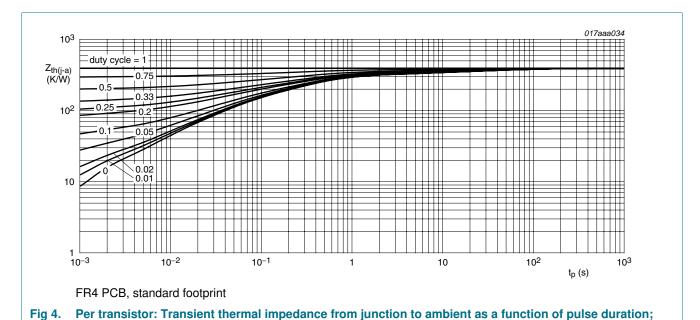
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6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per device						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	300	K/W
Per transis	tor					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	390	445	K/W
			[2] _	340	390	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		-	-	130	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



typical values

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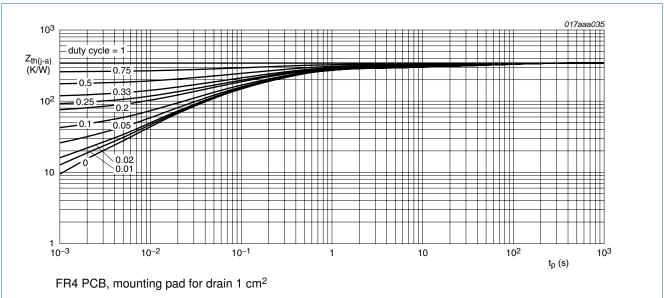


Fig 5. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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7. Characteristics

Table 7. Characteristics

Table 1.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics (per transistor)					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -10 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	-50	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	-1.1	-1.6	-2.1	V
I _{DSS}	drain leakage current	$V_{DS} = -50 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μΑ
		$V_{DS} = -50 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 ^{\circ}\text{C}$	-	-	-2	μΑ
I _{GSS}	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-10	μΑ
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-10	μΑ
R _{DSon}	drain-source on-state	$V_{GS} = -10 \text{ V}; I_D = -100 \text{ mA}; T_j = 25 \text{ °C}$	-	4.5	7.5	Ω
	resistance	$V_{GS} = -10 \text{ V}; I_D = -100 \text{ mA}; T_j = 150 \text{ °C}$	-	8	13.5	Ω
		$V_{GS} = -5 \text{ V}; I_D = -100 \text{ mA}; T_j = 25 \text{ °C}$	-	5.7	8.5	Ω
g _{fs}	forward transconductance	$V_{DS} = -10 \text{ V}; I_D = -100 \text{ mA}; T_j = 25 \text{ °C}$	-	150	-	mS
Dynamic	characteristics (per transistor)					
$Q_{G(tot)}$	total gate charge	$V_{DS} = -25 \text{ V}; I_D = -200 \text{ mA}; V_{GS} = -5 \text{ V};$	-	0.26	0.35	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.12	-	nC
Q_{GD}	gate-drain charge		-	0.09	-	nC
C _{iss}	input capacitance	$V_{DS} = -25 \text{ V; } f = 1 \text{ MHz; } V_{GS} = 0 \text{ V;}$	-	24	36	рF
C _{oss}	output capacitance	T _j = 25 °C	-	4.5	-	рF
C _{rss}	reverse transfer capacitance		-	1.3	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = -30 \text{ V}; R_L = 250 \Omega; V_{GS} = -10 \text{ V};$	-	13	26	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega$; $T_j = 25 °C$	-	11	-	ns
$t_{d(off)}$	turn-off delay time		-	48	96	ns
t _f	fall time		-	25	-	ns
Source-di	rain diode (per transistor)					
V_{SD}	source-drain voltage	$I_S = -115 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-0.48	-0.85	-1.2	V

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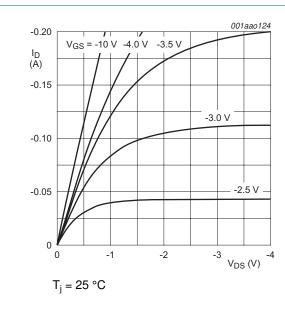
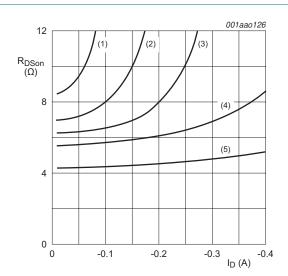


Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values



T_i = 25 °C

(1) $V_{GS} = -3.0 \text{ V}$

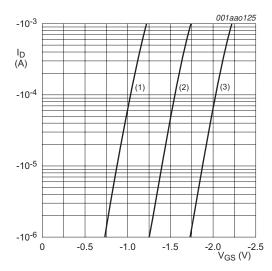
(2) $V_{GS} = -3.5 \text{ V}$

(3) $V_{GS} = -4.0 \text{ V}$

(4) $V_{GS} = -5.0 \text{ V}$

(5) $V_{GS} = -10.0 \text{ V}$

Fig 8. Drain-source on-state resistance as a function of drain current; typical values



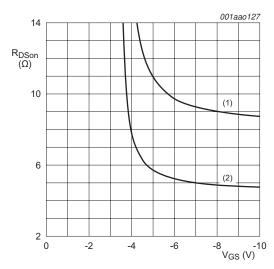
 $T_j = 25 \, ^{\circ}C; \, V_{DS} = -5 \, V$

(1) minimum values

(2) typical values

(3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage



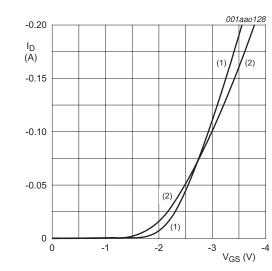
 $I_D = -200 \text{ mA}$

(1) $T_i = 150 \, ^{\circ}C$

(2) $T_i = 25 \, ^{\circ}C$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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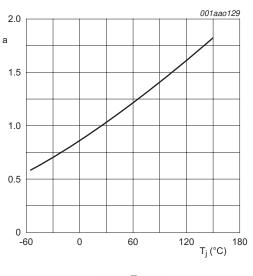


 $V_{DS} > I_D \times R_{DSon}$

(1)
$$T_j = 25 \, ^{\circ}C$$

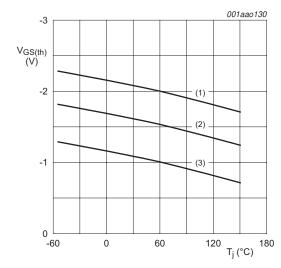
(2)
$$T_i = 150 \, ^{\circ}\text{C}$$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

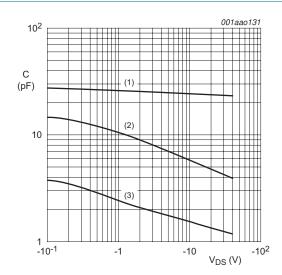
Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



 $I_D = -0.25 \text{ mA}; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig 12. Gate-source threshold voltage as a function of junction temperature

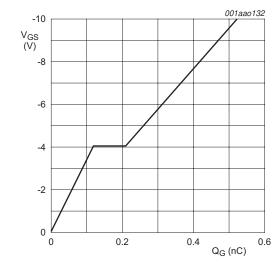


 $f = 1 MHz, V_{GS} = 0 V$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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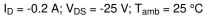


Fig 14. Gate-source voltage as a function of gate charge; typical values

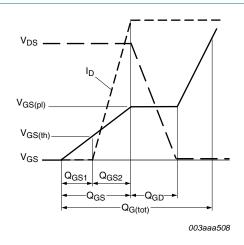
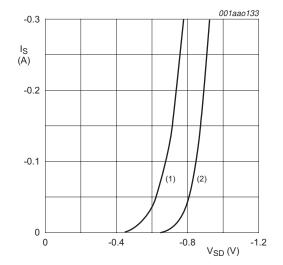


Fig 15. Gate charge waveform definitions



 $V_{GS} = 0 V$

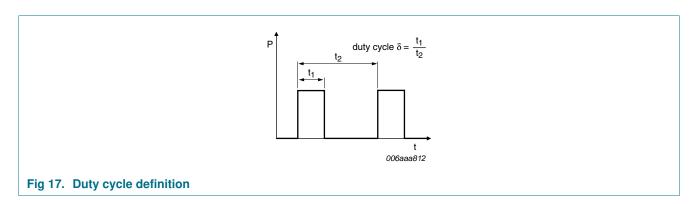
(1) $T_j = 150 \, ^{\circ}\text{C}$

(2) $T_i = 25 \, ^{\circ}C$

Fig 16. Source current as a function of source-drain voltage; typical values

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8. Test information



8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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9. Package outline

Plastic surface-mounted package; 6 leads

SOT363

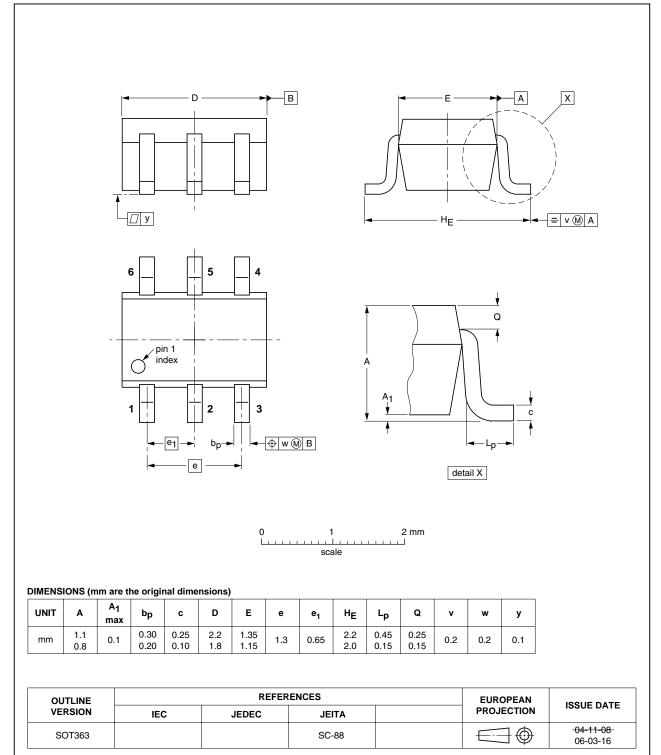


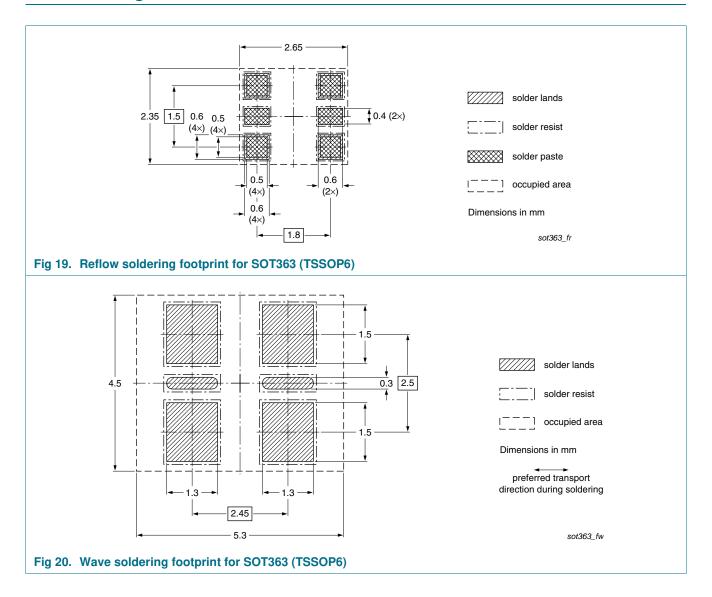
Fig 18. Package outline SOT363 (TSSOP6)

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10. Soldering



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11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BSS84AKS v.2	20110523	Product data sheet	-	-

50 V, 160 mA dual P-channel Trench MOSFET

12. Legal information

12.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
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